

Broad-band GaN-based UV photodiode



Description

Broad band GaN based UV photodiode, it is
Optimized for ultra-violet range 210~370nm, UVB and UVC wavelength
Can be easily selected with integral filters. It is packaged in electrically
Isolated and hermetically sealed TO-46 mental can with quarts window.

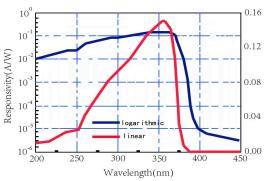
Features

- * High reliability in demanding environments
- * Operating temperature is from -40 to +80 $^{\circ}\mathrm{C}$
- * Storage temperature is from -40 to +120 $^{\circ}\mathrm{C}$

Applications

- * Sunlight exposure meter
- * UV power meter
- * Water purification facilities
- * flame detection

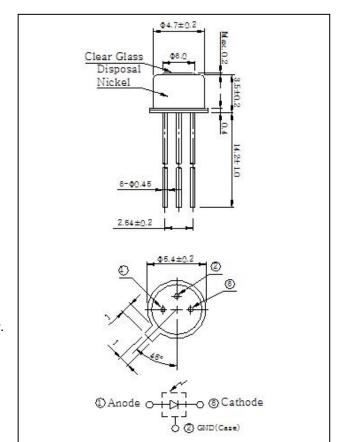
Spectral response



Wavelength(nm)

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission.

Specifications are subject change without notice

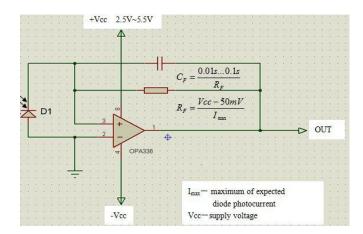




Specifications:

Parameters	Symbol	Value	Unit
Maximum ratings			aco :
Operation temperature range	Topt	-25-85	°C
Storage temperature range	T _{sto}	-40-85	°C
Soldering temperature (3 s)	T _{sol}	260	°C
Reverse voltage	V_{r-max}	-10	V
General characteristics (25 °C)			
Chip size	А	1	mm ²
Dark current (V _r = -1 V)	l _d	<1	nA
Photo current (1 mW/cm ² at 360 nm)	l _{ph}	1200	nA
Temperature coefficient	T _c	-0.1	%/°C
Capacitance	C _p	37	pF
Spectral response characteristics (25 °C)			79
Wavelength of peak responsivisity	? _p	355	nm
Peak responsivisity (at 355 nm)	R _{max}	0.15	A/W
Spectral response range (R=0.1×R _{max})		210-375	nm
UV-visible rejection ratio (R _{max} /R _{400 nm})	-	>104	-

Typical application circuit



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